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# A nanostructure platform for live-cell manipulation of membrane curvature

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Curvature measurements on the nanostructures.

The measurements of the curvatures designed in the nanostructures are labeled in the top view. "D" denotes diameter. The values of the curvatures are listed in Supplementary Table 1. There are also flat surfaces as a control in the design, such as the side walls of the nanobar (b) and the I in CUI (c).



Microbubbles in FIB–SEM.

Air trapped in resin deforms cellular structure. Scale, 1  $\mu m.$ 



Optical micrograph of defects after liftoff.

The regions of missing Cr masks are indicated by the red arrows. Scale bar, 5  $\mu m.$ 



Substrate piece placed on a carrier wafer for dry etching.

The substrate piece is cut into four pieces. Vacuum pump oil is applied between the substrate piece and dummy wafer.



Surface chemistry for immobilizing ECM proteins.



Selection of ends and centers on a nanobar.

This is a crop from U2-OS DNM2-EGFP fluorescence image (5  $\mu$ m by 5  $\mu$ m), generated. The small blue masks select the centers on both sides of the nanobar. The small red masks select the ends of the nanobar. The intensity values are read in a customized MATLAB program. The total intensity of the ends is divided by the total intensity of the centers to obtain a ratio for a given nanobar. Scale bar, 1  $\mu$ m.



Cracks in samples in FIB–SEM.

Scale bar, 5 µm.



Charging effect in FIB-SEM imaging.

Scale bar, 5 µm.



Cross-sectioning in FIB-SEM.

a, Secondary electron imaging. b, Location of a region of interest. d, Pt deposition. d, Trenching. Scale bars, 1 µm.



Curtaining effect.

Sample is tilted to 52°.



Collapsed nanopillars after dry etching.

Nanopillars are 200 nm in diameter and 1  $\mu m$  in height. Scale bar, 5  $\mu m.$ 

Curvature label	Curvature value in the design	Curvature orientation
D1	200, 500 and 1000 nm	Positive
D2	100, 200, 300, 400, 500, 600, 700, 800,	Positive
	and 1000 nm	
D3	100, 200, 300, 400, 500, 600, 700, 800,	Positive
	and 1000 nm (the same as D2)	
D4	1000 nm	Positive
D5	600 nm	Negative
D6	600 nm	Negative
D7	1000 nm	Positive
Supplementary Table 1		
Curvature values in the design.		
The curvatures are labeled in Supplementary Fig. 1.		